

OSADA et al.
Appln. No. 10/540,514
Preliminary Amendment

AMENDMENTS TO THE SPECIFICATION

**Please replace the paragraph bridging pages 4 and 5 of the present specification
with the following amended paragraph:**

A limit value of a thickness of the strain crystal layer in the above described lattice misfit material are given as a function of the strain crystal layer composition, and as for an InGaAs layer with respect to a GaAs layer for example, a Matthews' theoretical equation disclosed in J. Crystal Growth, 27 (1974) p.118 and in J. Crystal Growth, 32 ~~(1974)~~(1976) p.265, is known, and this theoretical equation has been found to be experimentally correct as a whole.